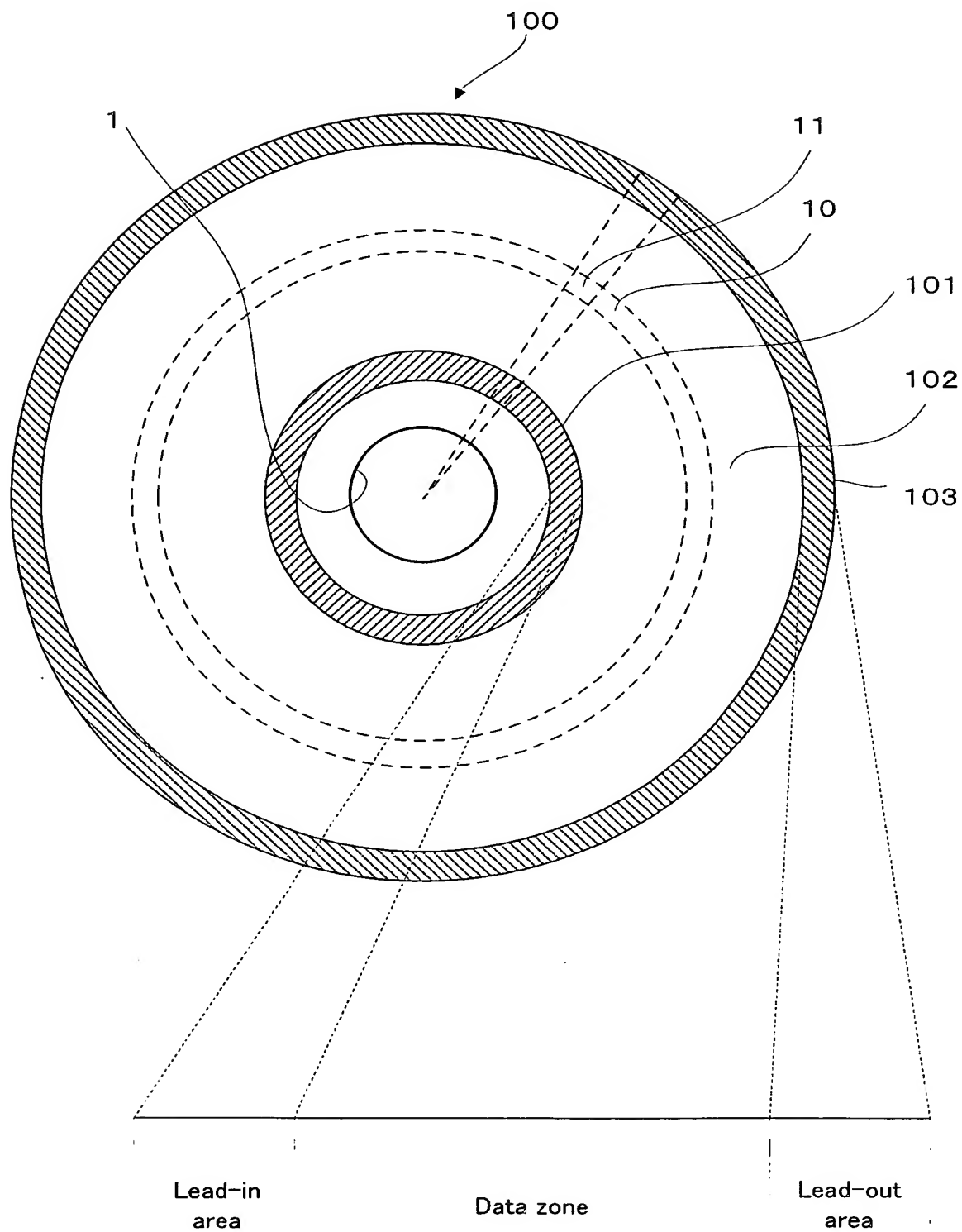


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[FIG. 1]



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[FIG. 2]

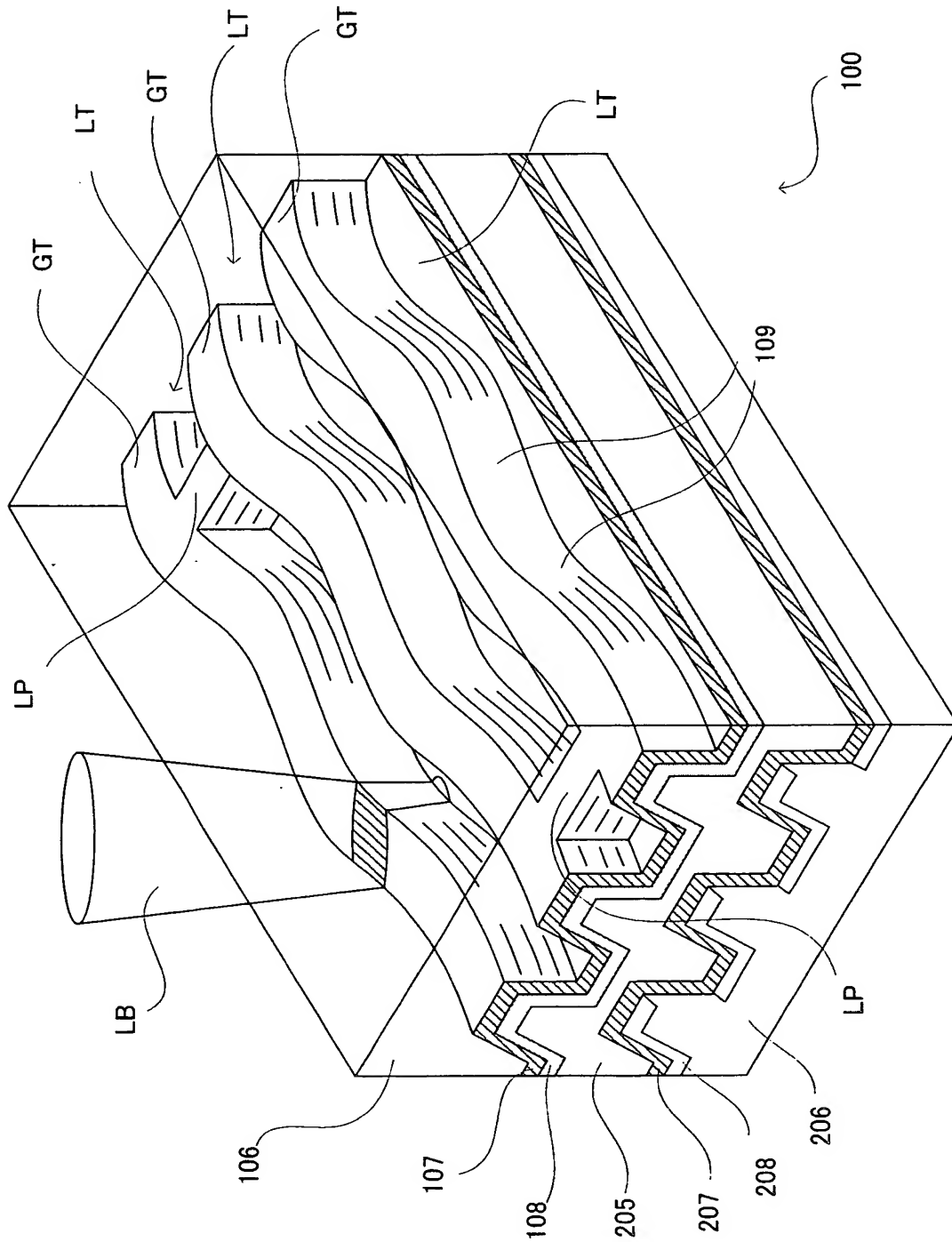


Fig. 3] Cross-sectional view of a semiconductor device. The device consists of a repeating structure of L1 layer and L0 layer. The L1 layer contains a gate (GT) and a light-transmitting (LT) region. The L0 layer contains a gate (GT) and a light-transmitting (LT) region. The structure is labeled with 100, 206, 208, 207, 205, 105, 108, 107, and 106.

G. 4]

A cross-sectional view of a semiconductor device 100a. The device features a periodic structure with alternating raised and recessed regions. The top layer is labeled L1 layer, and the bottom layer is labeled L0 layer. The structure includes a central channel region 105, a gate region 106, and a source/drain region 107. The gate region 106 is formed by a gate stack 108, which includes a gate oxide layer 105 and a gate electrode layer 107. The source/drain region 107 is formed by a source/drain oxide layer 105 and a source/drain electrode layer 107. The raised regions are labeled 206, 207, 208a, and 205. The recessed regions are labeled S21 and S20. The device 100a is shown in a perspective view, with a dashed line indicating the cross-section.

100a

L1 layer

S21

S20

L0 layer

206

208a

207

205

105

108

107

106

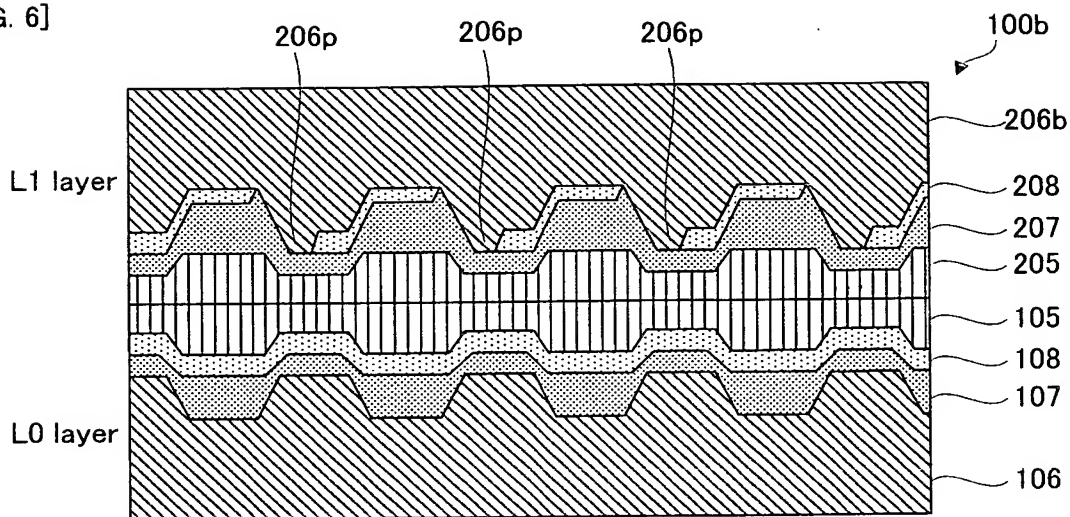
206

208

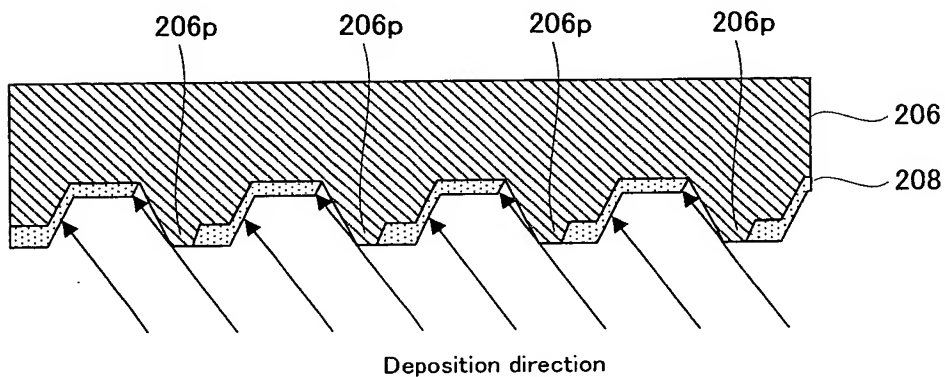
Deposition direction

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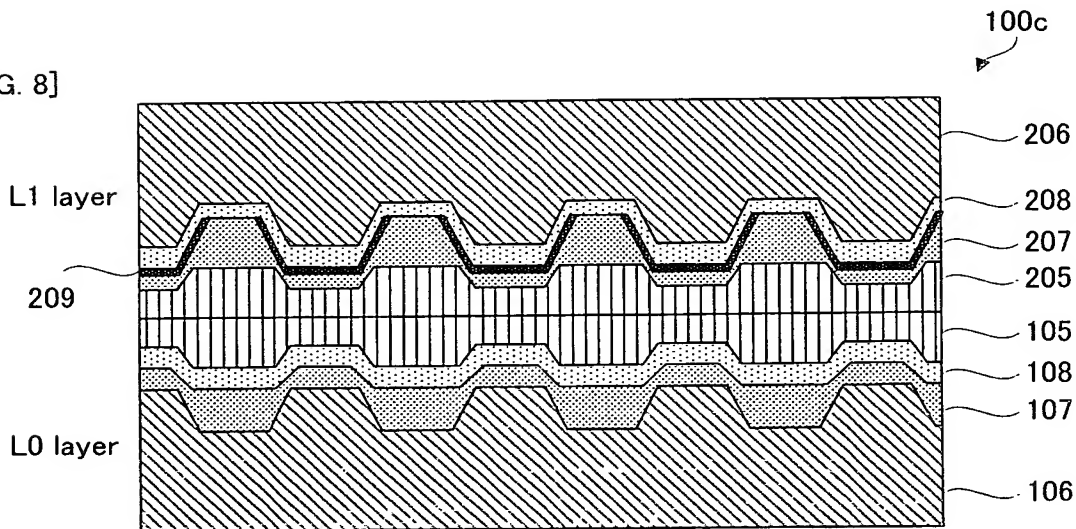
[FIG. 6]



[FIG. 7]

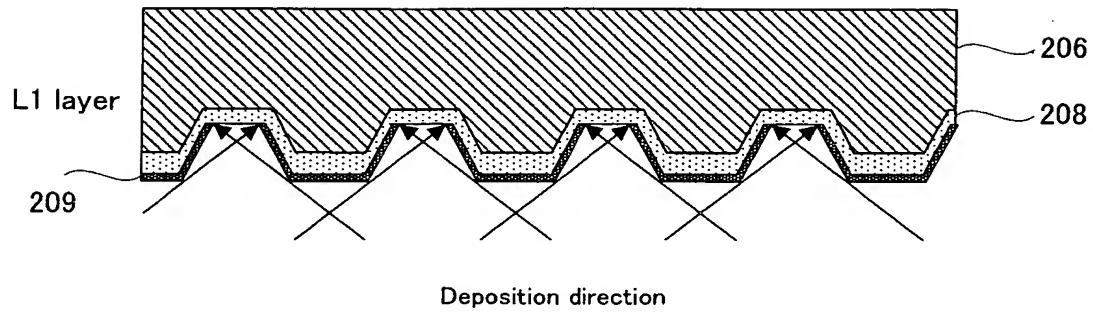


[FIG. 8]



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[FIG. 9]



[FIG. 10]

